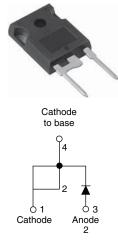
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 25 A



TO-247AC modified

PRODUCT SUMMARY									
Package	TO-247AC modified (2 pins)								
I _{F(AV)}	25 A								
V _R	600 V								
V _F at I _F	1.7 V								
t _{rr} (typ.)	23 ns								
T _J max.	150 °C								
Diode variation	Single die								

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA25PB60PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A continuous current, the VS-HFA25PB60PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA25PB60PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		600	V					
Maximum continuous forward current	I _F	T _C = 100 °C	25						
Single pulse forward current	I _{FSM}		225	А					
Maximum repetitive forward current	I _{FRM}		100						
Maximum power discinction	р	T _C = 25 °C	151	W					
Maximum power dissipation	P _D	T _C = 100 °C	60	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C					

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(e3) RoHS

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	600	-	-				
Maximum forward voltage		I _F = 25 A		-	1.3	1.7	V		
	V _{FM}	I _F = 50 A	See fig. 1	-	1.5	2.0			
		I _F = 25 A, T _J = 125 °C		-	1.3	1.7			
Maximum reverse	I _{RM}	V _R = V _R rated	See fig. 0	-	1.5	20	μA		
leakage current		$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	600	2000			
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	55	100	pF		
Series inductance	L _S	Measured lead to lead 5 mm from body	-	12	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time See fig. 5, 10	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	0 A/µs, V _R = 30 V	-	23	-	ns		
	t _{rr1}	T _J = 25 °C		-	50	75			
	t _{rr2}	T _J = 125 °C		-	105	160			
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 25 A dI _F /dt = 200 A/μs V _R = 200 V	-	4.5	10	A nC Α/μs		
See fig. 6, 10	I _{RRM2}	T _J = 125 °C		-	8.0	15			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	112	375			
See fig. 7, 10	Q _{rr2}	T _J = 125 °C		-	420	1200			
Peak rate of fall of recovery current during t _b	dl _{(rec)M} /dt1	T _J = 25 °C		-	250	-			
See fig. 8, 10	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-	Αγμο		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	0.83					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-					
Weight			-	6.0	-	g				
weight			-	0.21	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC modified (JEDEC)	HFA25PB60							

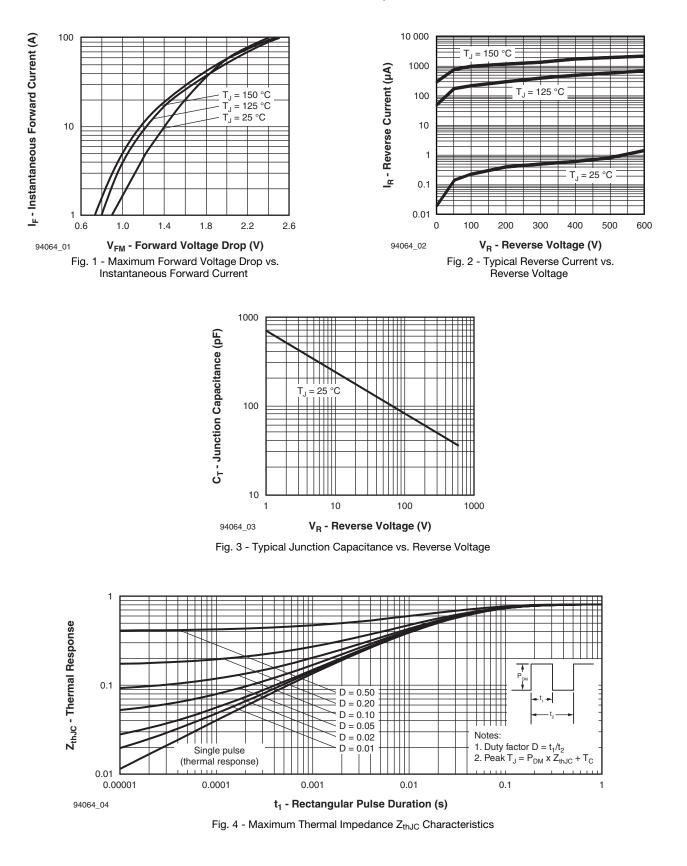
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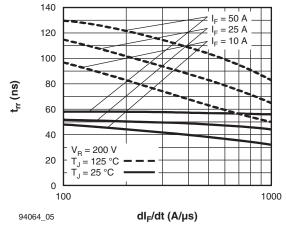


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

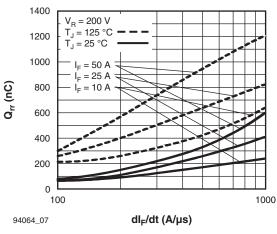


Fig. 7 - Typical Stored Charge vs. dl_F/dt

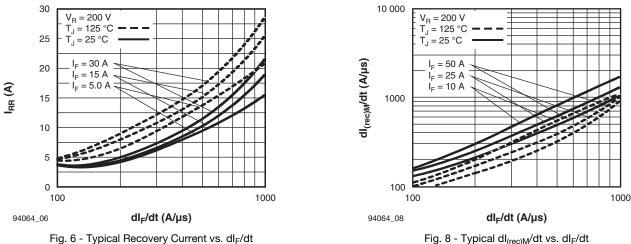


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

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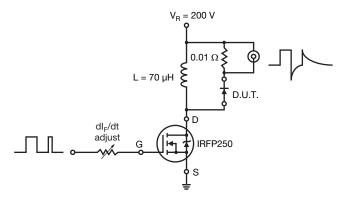


Fig. 9 - Reverse Recovery Parameter Test Circuit

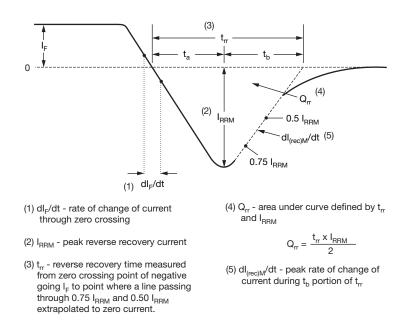


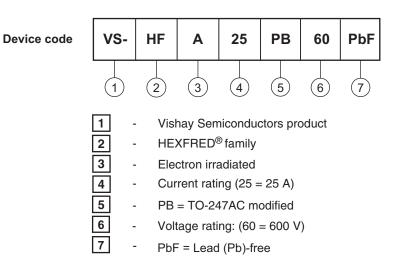
Fig. 1 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE



LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95253							
Part marking information	www.vishay.com/doc?95255							

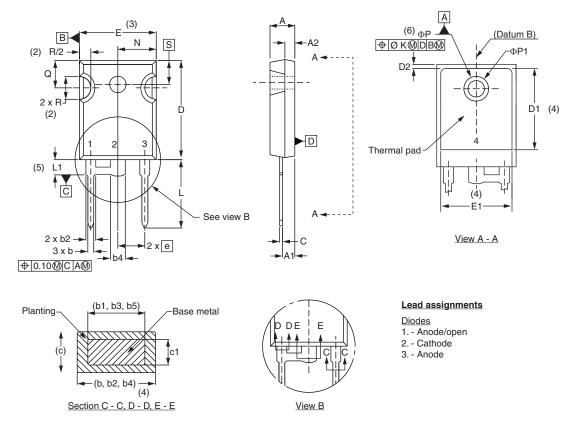
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Outline Dimensions





DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	HES	NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STINDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209			D2	0.51	1.30	0.020	0.051	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.50	2.49	0.059	0.098			E1	13.72	-	0.540	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ΦK	2.	54	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.37	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0.3		
b5	2.59	3.38	0.102	0.133			ΦР	3.56	3.66	0.14	0.144	
С	0.38	0.86	0.015	0.034			Φ P1	-	6.98	-	0.275	
c1	0.38	0.76	0.015	0.030			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	1.78	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC	

Notes

⁽¹⁾ Dimensioning and tolerance per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

- ⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1

(6) ΦP to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC outline TO-247 with exception of dimension c

Revision: 21-Jun-11

1

Document Number: 95253

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